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Practitioner's Docket No. MI22-2500

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: David L. Dickerson et al.

Application No.: 10/799,794
Filed: 03/11/04

Group No.: 2814
Examiner: A. Mai

For: Isolation Region Forming Methods

Commissioner for Patents
Washington, D.C. 20231


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 10/799,794
Filing Date March 11, 2004
Inventor David L. Dickerson et al.
Assignee Micron Technology, Inc.
Group Art Unit 2814
Examiner A.D. Mai
Attorney's Docket No. MI22-2500
Title: Isolation Region Forming Methods

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - - See attached Form PTO-1449


The attached Form PTO-1449 is submitted in compliance with 37 C.F.R. §§ 1.56. Pursuant to Federal Register Vol. 69, No. 182, pg. 56542 (September 21, 2004), no copies of any cited U.S. patents or U.S. published applications are included herewith. Copies of all other cited art references, if any, are attached. No admission is made regarding whether the submitted reference is prior art.

Citation of this reference is respectfully requested.

Respectfully submitted,

Date:

3-23-05


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Form PTO-149		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. N122-2500		SERIAL NO. 10799,794	
LIST OF ART CITED BY APPLICANT <small>(Use several sheets if necessary)</small>					APPLICANT David L. Dickerson et al.			
					FILING DATE March 11, 2004		GROUP 2814	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA							
	AB							
	AC							
	AD							
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AR		K. One et al., "Narrow-Width Effects of Shallow Trench-Isolated CMOS with n+ -Polysilicon					
			Gate," IEEE Vol. 36, © 1989, pgs. 1110-1118.					
	AS							
	AT							
EXAMINER				DATE CONSIDERED				
<small>*EXAMINER: Initial if reference considered, =braker or not citation is in conformance with MPEP 609; D= line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								